



Welcome to [E-XFL.COM](https://www.e-xfl.com)

Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	147
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3pe1500-2pq208i

Specify I/O States During Programming

Load from file... Save to file... ☐ Show BSR Details

	Port Name	Macro Cell	Pin Number	I/O State (Output Only)
	BIST	ADLIB:INBUF	T2	1
	BYPASS_IO	ADLIB:INBUF	K1	1
	CLK	ADLIB:INBUF	B1	1
	ENOUT	ADLIB:INBUF	J16	1
	LED	ADLIB:OUTBUF	M3	0
	MONITOR[0]	ADLIB:OUTBUF	B5	0
	MONITOR[1]	ADLIB:OUTBUF	C7	Z
	MONITOR[2]	ADLIB:OUTBUF	D9	Z
	MONITOR[3]	ADLIB:OUTBUF	D7	Z
	MONITOR[4]	ADLIB:OUTBUF	A11	Z
	OEa	ADLIB:INBUF	E4	Z
	OEb	ADLIB:INBUF	F1	Z
	OSC_EN	ADLIB:INBUF	K3	Z
	PAD[10]	ADLIB:BIBUF_LVCMOS33U	M8	Z
	PAD[11]	ADLIB:BIBUF_LVCMOS33D	R7	Z
	PAD[12]	ADLIB:BIBUF_LVCMOS33U	D11	Z
	PAD[13]	ADLIB:BIBUF_LVCMOS33D	C12	Z
	PAD[14]	ADLIB:BIBUF_LVCMOS33U	R6	Z

Help OK Cancel

Figure 1-3 • I/O States During Programming Window

- Click OK to return to the FlashPoint – Programming File Generator window.

I/O States during programming are saved to the ADB and resulting programming files after completing programming file generation.

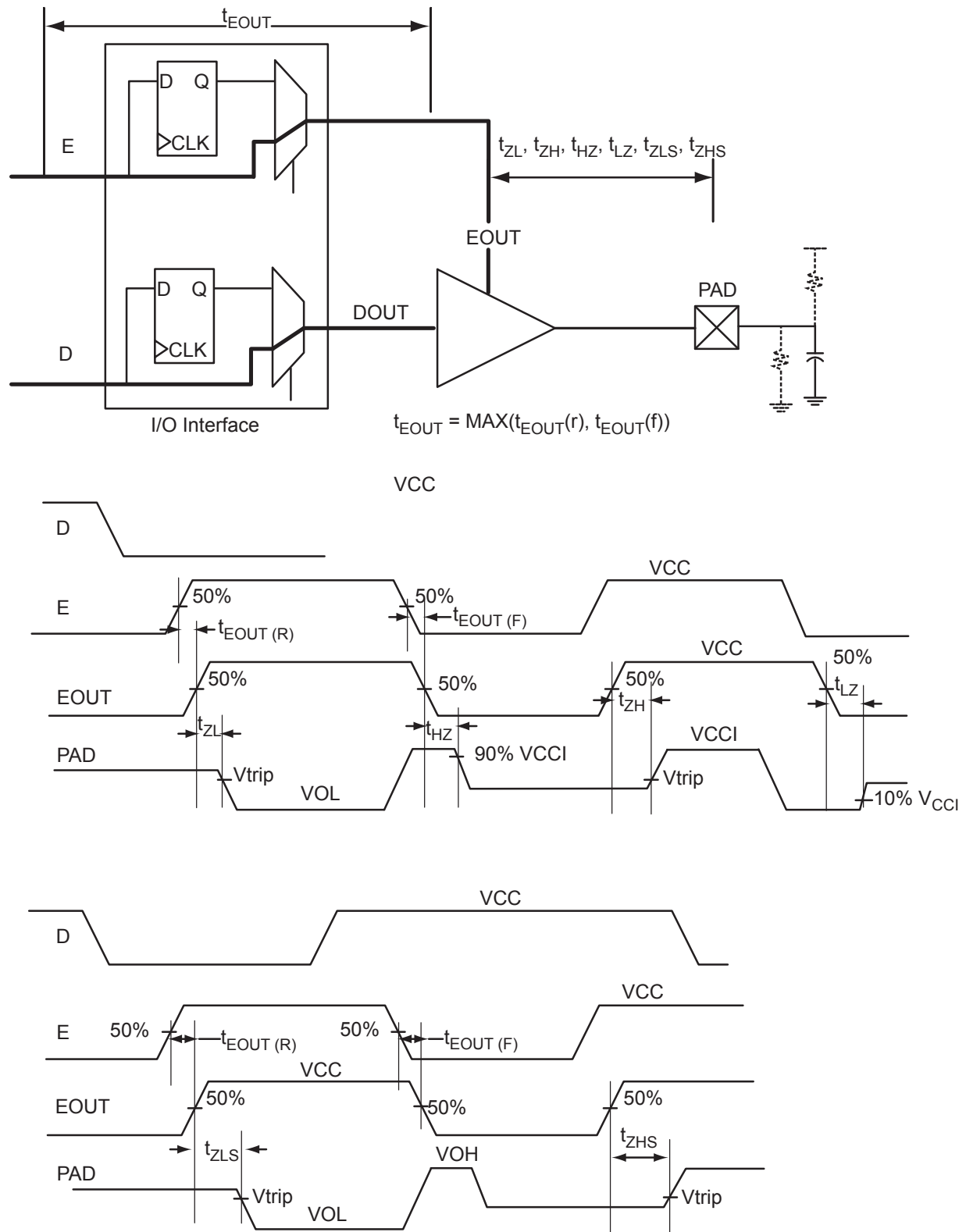


Figure 2-5 • Tristate Output Buffer Timing Model and Delays (example)

Summary of I/O Timing Characteristics – Default I/O Software Settings

Table 2-15 • Summary of AC Measuring Points

Standard	Input Reference Voltage (VREF_TYP)	Board Termination Voltage (VTT_REF)	Measuring Trip Point (Vtrip)
3.3 V LVTTTL / 3.3 V LVCMOS	–	–	1.4 V
3.3 V LVCMOS Wide Range	–	–	1.4 V
2.5 V LVCMOS	–	–	1.2 V
1.8 V LVCMOS	–	–	0.90 V
1.5 V LVCMOS	–	–	0.75 V
3.3 V PCI	–	–	0.285 * VCCI (RR) 0.615 * VCCI (FF))
3.3 V PCI-X	–	–	0.285 * VCCI (RR) 0.615 * VCCI (FF)
3.3 V GTL	0.8 V	1.2 V	VREF
2.5 V GTL	0.8 V	1.2 V	VREF
3.3 V GTL+	1.0 V	1.5 V	VREF
2.5 V GTL+	1.0 V	1.5 V	VREF
HSTL (I)	0.75 V	0.75 V	VREF
HSTL (II)	0.75 V	0.75 V	VREF
SSTL2 (I)	1.25 V	1.25 V	VREF
SSTL2 (II)	1.25 V	1.25 V	VREF
SSTL3 (I)	1.5 V	1.485 V	VREF
SSTL3 (II)	1.5 V	1.485 V	VREF
LVDS	–	–	Cross point
LVPECL	–	–	Cross point

Table 2-16 • I/O AC Parameter Definitions

Parameter	Definition
t _{DP}	Data to Pad delay through the Output Buffer
t _{PY}	Pad to Data delay through the Input Buffer with Schmitt trigger disabled
t _{DOUT}	Data to Output Buffer delay through the I/O interface
t _{EOUT}	Enable to Output Buffer Tristate Control delay through the I/O interface
t _{DIN}	Input Buffer to Data delay through the I/O interface
t _{PYS}	Pad to Data delay through the Input Buffer with Schmitt trigger enabled
t _{HZ}	Enable to Pad delay through the Output Buffer—High to Z
t _{ZH}	Enable to Pad delay through the Output Buffer—Z to High
t _{LZ}	Enable to Pad delay through the Output Buffer—Low to Z
t _{ZL}	Enable to Pad delay through the Output Buffer—Z to Low
t _{ZHS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to High
t _{ZLS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to Low

Table 2-17 • Summary of I/O Timing Characteristics—Software Default Settings
–2 Speed Grade, Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$,
Worst-Case $V_{CCI} = 3.0\text{ V}$

I/O Standard	Drive Strength (mA)	Equivalent Software Default Drive Strength Option) ¹	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{PYS} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)
3.3 V LVTTTL / 3.3 V LVCMOS	12	12	High	35	–	0.49	2.74	0.03	0.90	1.17	0.32	2.79	2.14	2.45	2.70	4.46	3.81
3.3 V LVCMOS Wide Range ²	100 μA	12	High	35	–	0.49	4.24	0.03	1.36	1.78	0.32	4.24	3.25	3.78	4.17	6.77	5.79
2.5 V LVCMOS	12	12	High	35	–	0.49	2.80	0.03	1.13	1.24	0.32	2.85	2.61	2.51	2.61	4.52	4.28
1.8 V LVCMOS	12	12	High	35	–	0.49	2.83	0.03	1.08	1.42	0.32	2.89	2.31	2.79	3.16	4.56	3.98
1.5 V LVCMOS	12	12	High	35	–	0.49	3.30	0.03	1.27	1.60	0.32	3.36	2.70	2.96	3.27	5.03	4.37
3.3 V PCI	Per PCI spec	–	High	10	25 ³	0.49	2.09	0.03	0.78	1.17	0.32	2.13	1.49	2.45	2.70	3.80	3.16
3.3 V PCI-X	Per PCI-X spec	–	High	10	25 ³	0.49	2.09	0.03	0.78	1.17	0.32	2.13	1.49	2.45	2.70	3.80	3.16
3.3 V GTL	20 ⁴	–	High	10	25	0.45	1.55	0.03	2.19	–	0.32	1.52	1.55	–	–	3.19	3.22
2.5 V GTL	20 ⁴	–	High	10	25	0.45	1.59	0.03	1.83	–	0.32	1.61	1.59	–	–	3.28	3.26
3.3 V GTL+	35	–	High	10	25	0.45	1.53	0.03	1.19	–	0.32	1.56	1.53	–	–	3.23	3.20
2.5 V GTL+	33	–	High	10	25	0.45	1.65	0.03	1.13	–	0.32	1.68	1.57	–	–	3.35	3.24
HSTL (I)	8	–	High	20	50	0.49	2.37	0.03	1.59	–	0.32	2.42	2.35	–	–	4.09	4.02
HSTL (II)	15 ⁴	–	High	20	25	0.49	2.26	0.03	1.59	–	0.32	2.30	2.03	–	–	3.97	3.70
SSTL2 (I)	15	–	High	30	50	0.49	1.59	0.03	1.00	–	0.32	1.62	1.38	–	–	3.29	3.05
SSTL2 (II)	18	–	High	30	25	0.49	1.62	0.03	1.00	–	0.32	1.65	1.32	–	–	3.32	2.99
SSTL3 (I)	14	–	High	30	50	0.49	1.72	0.03	0.93	–	0.32	1.75	1.37	–	–	3.42	3.04
SSTL3 (II)	21	–	High	30	25	0.49	1.54	0.03	0.93	–	0.32	1.57	1.25	–	–	3.24	2.92
LVDS/B-LVDS/M-LVDS	24	–	High	–	–	0.49	1.40	0.03	1.36	–	–	–	–	–	–	–	–
LVPECL	24	–	High	–	–	0.49	1.36	0.03	1.22	–	–	–	–	–	–	–	–

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3V wide range as specified in the JESD8b specification.
3. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See [Figure 2-11 on page 2-38](#) for connectivity. This resistor is not required during normal operation.
4. Output drive strength is below JEDEC specification.
5. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#).

Timing Characteristics

Table 2-31 • 3.3 V LVCMOS Wide Range High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.7\text{ V}$

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 μA	4 mA	Std.	0.66	12.19	0.04	1.83	2.38	0.43	12.19	10.17	4.16	4.00	15.58	13.57	ns
		–1	0.56	10.37	0.04	1.55	2.02	0.36	10.37	8.66	3.54	3.41	13.26	11.54	ns
		–2	0.49	9.10	0.03	1.36	1.78	0.32	9.10	7.60	3.11	2.99	11.64	10.13	ns
100 μA	8 mA	Std.	0.66	7.85	0.04	1.83	2.38	0.43	7.85	6.29	4.71	4.97	11.24	9.68	ns
		–1	0.56	6.68	0.04	1.55	2.02	0.36	6.68	5.35	4.01	4.22	9.57	8.24	ns
		–2	0.49	5.86	0.03	1.36	1.78	0.32	5.86	4.70	3.52	3.71	8.40	7.23	ns
100 μA	12 mA	Std.	0.66	5.67	0.04	1.83	2.38	0.43	5.67	4.36	5.06	5.59	9.07	7.75	ns
		–1	0.56	4.82	0.04	1.55	2.02	0.36	4.82	3.71	4.31	4.75	7.71	6.59	ns
		–2	0.49	4.24	0.03	1.36	1.78	0.32	4.24	3.25	3.78	4.17	6.77	5.79	ns
100 μA	16 mA	Std.	0.66	5.35	0.04	1.83	2.38	0.43	5.35	3.96	5.15	5.76	8.75	7.35	ns
		–1	0.56	4.55	0.04	1.55	2.02	0.36	4.55	3.36	4.38	4.90	7.44	6.25	ns
		–2	0.49	4.00	0.03	1.36	1.78	0.32	4.00	2.95	3.85	4.30	6.53	5.49	ns
100 μA	24 mA	Std.	0.66	4.96	0.04	1.83	2.38	0.43	4.96	3.27	5.23	6.38	8.35	6.67	ns
		–1	0.56	4.22	0.04	1.55	2.02	0.36	4.22	2.78	4.45	5.43	7.11	5.67	ns
		–2	0.49	3.70	0.03	1.36	1.78	0.32	3.70	2.44	3.91	4.76	6.24	4.98	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. Software default selection highlighted in gray.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

Table 2-84 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{ISUE}	Enable Setup Time for the Input Data Register	B, A
t_{IHE}	Enable Hold Time for the Input Data Register	B, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

Note: *See Figure 2-25 on page 2-53 for more information.

Table 2-85 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t_{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t_{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t_{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

Note: *See Figure 2-26 on page 2-55 for more information.

Output DDR Module

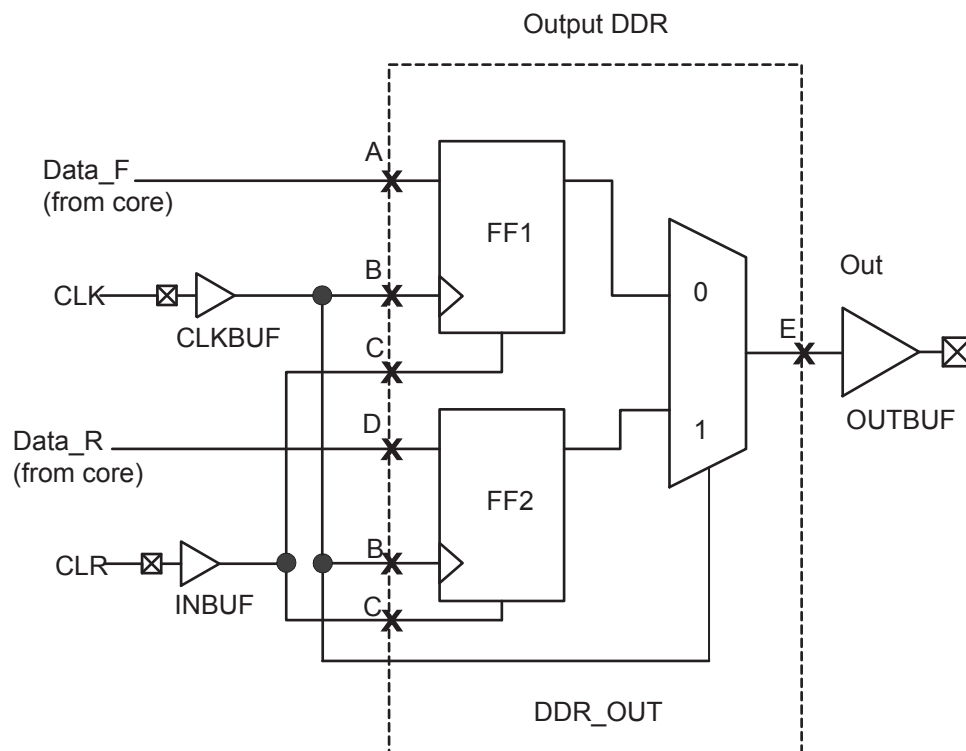


Figure 2-32 • Output DDR Timing Model

Table 2-91 • Parameter Definitions

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
$t_{DDROCLKQ}$	Clock-to-Out	B, E
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out	C, E
$t_{DDROREMCLR}$	Clear Removal	C, B
$t_{DDRORECCLR}$	Clear Recovery	C, B
$t_{DDROSUD1}$	Data Setup Data_F	A, B
$t_{DDROSUD2}$	Data Setup Data_R	D, B
$t_{DDROHD1}$	Data Hold Data_F	A, B
$t_{DDROHD2}$	Data Hold Data_R	D, B

Timing Characteristics

Table 2-93 • Combinatorial Cell Propagation Delays
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Combinatorial Cell	Equation	Parameter	-2	-1	Std.	Units
INV	$Y = !A$	t_{PD}	0.40	0.46	0.54	ns
AND2	$Y = A \cdot B$	t_{PD}	0.47	0.54	0.63	ns
NAND2	$Y = !(A \cdot B)$	t_{PD}	0.47	0.54	0.63	ns
OR2	$Y = A + B$	t_{PD}	0.49	0.55	0.65	ns
NOR2	$Y = !(A + B)$	t_{PD}	0.49	0.55	0.65	ns
XOR2	$Y = A \oplus B$	t_{PD}	0.74	0.84	0.99	ns
MAJ3	$Y = \text{MAJ}(A, B, C)$	t_{PD}	0.70	0.79	0.93	ns
XOR3	$Y = A \oplus B \oplus C$	t_{PD}	0.87	1.00	1.17	ns
MUX2	$Y = A \text{ IS } + B \text{ S}$	t_{PD}	0.51	0.58	0.68	ns
AND3	$Y = A \cdot B \cdot C$	t_{PD}	0.56	0.64	0.75	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

VersaTile Specifications as a Sequential Module

The ProASIC3E library offers a wide variety of sequential cells, including flip-flops and latches. Each has a data input and optional enable, clear, or preset. In this section, timing characteristics are presented for a representative sample from the library. For more details, refer to the [Fusion](#), [IGLOO/e](#), and [ProASIC3/E Macro Library Guide](#).

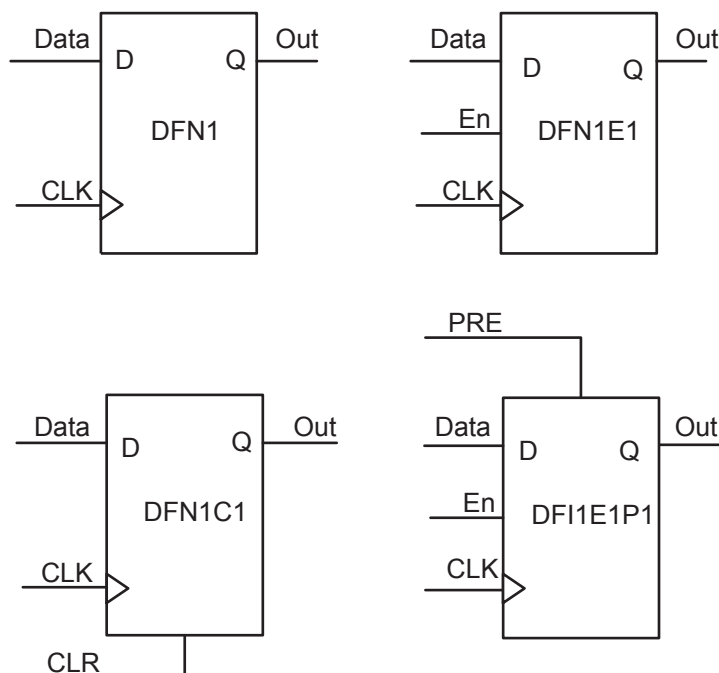


Figure 2-36 • Sample of Sequential Cells

Timing Characteristics

Table 2-95 • A3PE600 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2		-1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.83	1.04	0.94	1.18	1.11	1.39	ns
t_{RCKH}	Input High Delay for Global Clock	0.81	1.06	0.93	1.21	1.09	1.42	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.25		0.28		0.33	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

Table 2-96 • A3PE1500 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2		-1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.07	1.29	1.22	1.47	1.43	1.72	ns
t_{RCKH}	Input High Delay for Global Clock	1.06	1.32	1.21	1.50	1.42	1.76	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

Table 2-97 • A3PE3000 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2		-1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.41	1.62	1.60	1.85	1.88	2.17	ns
t_{RCKH}	Input High Delay for Global Clock	1.40	1.66	1.59	1.89	1.87	2.22	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.35	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

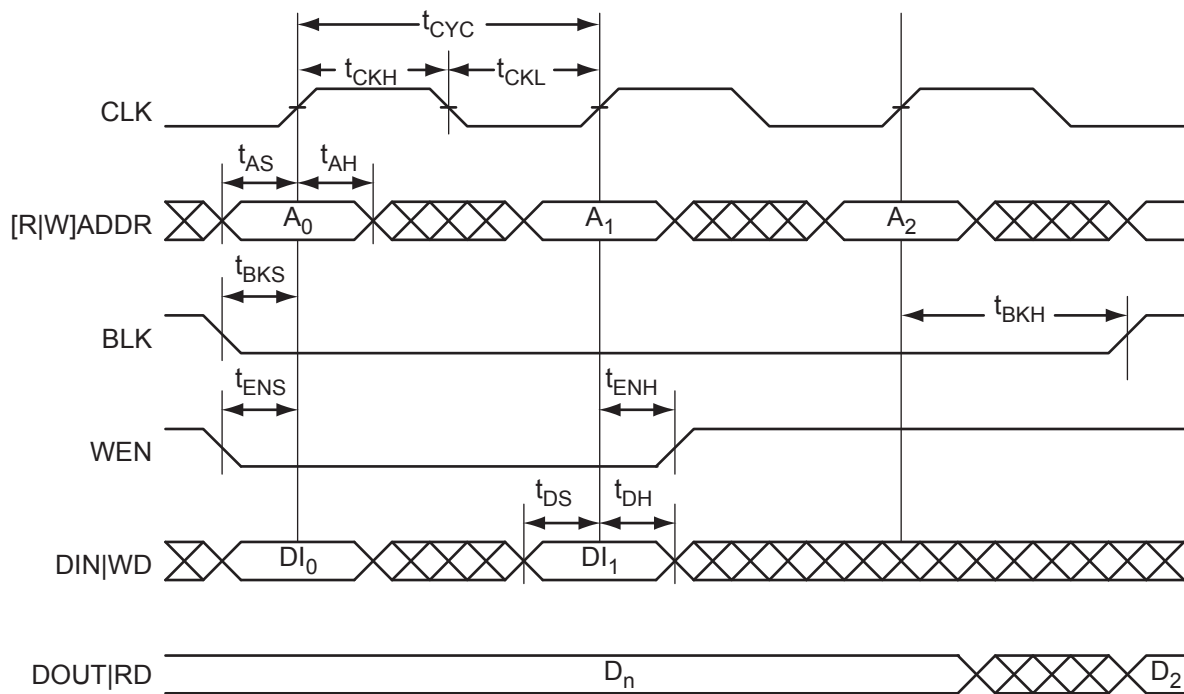


Figure 2-43 • RAM Write, Output Retained. Applicable to Both RAM4K9 and RAM512x18.

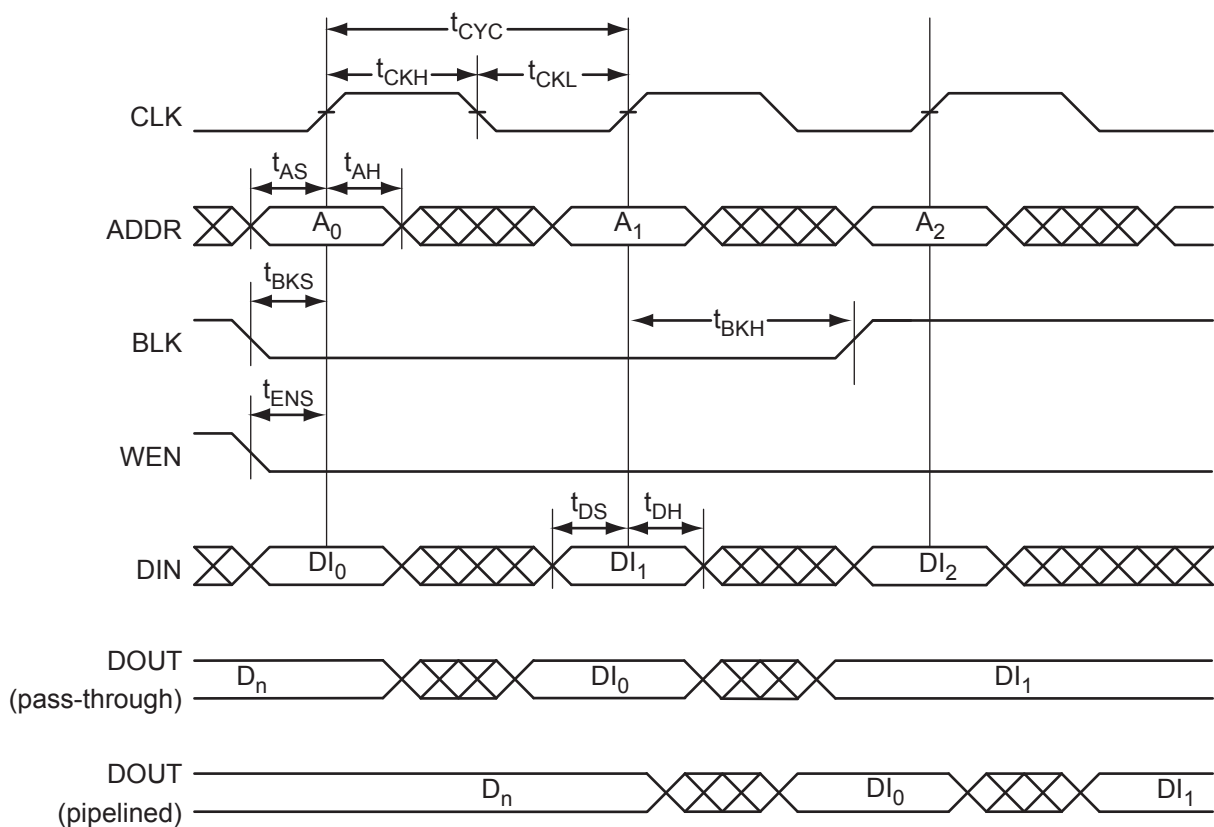


Figure 2-44 • RAM Write, Output as Write Data. Applicable to RAM4K9 Only.

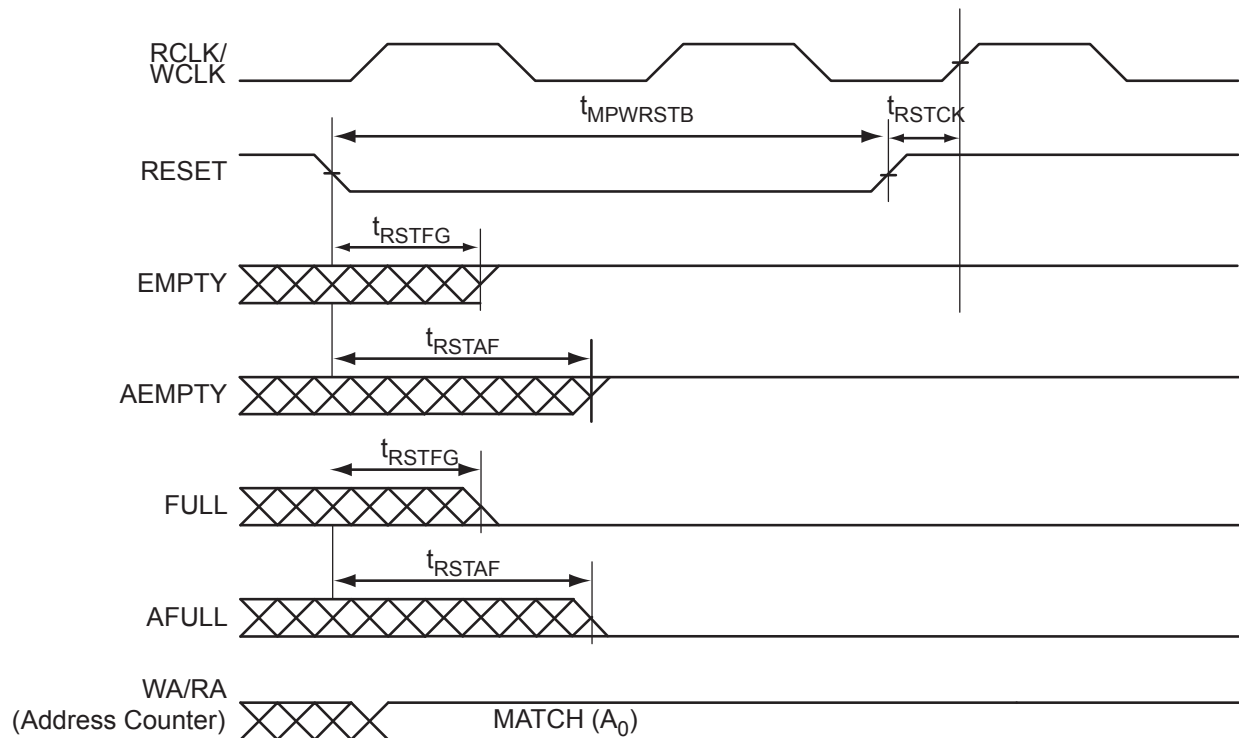


Figure 2-49 • FIFO Reset

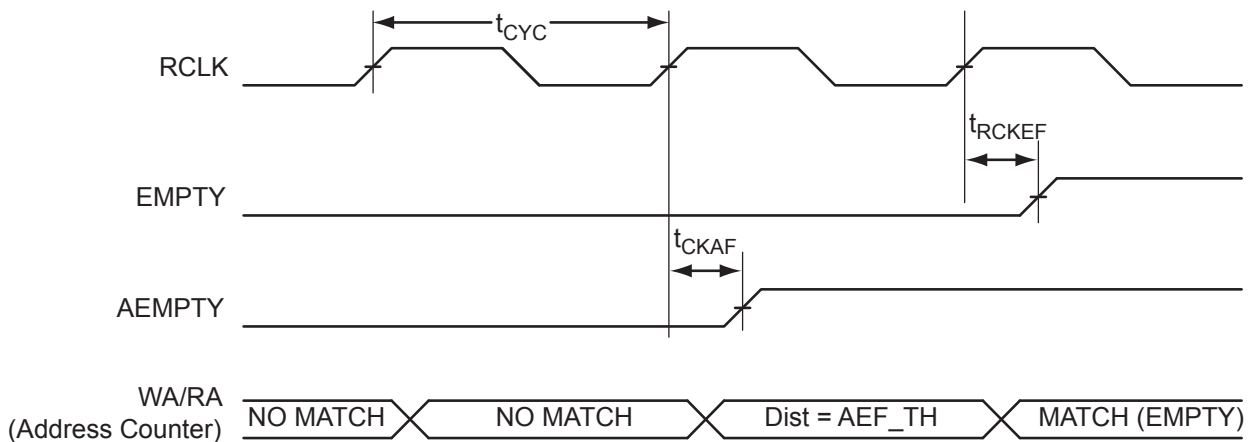


Figure 2-50 • FIFO EMPTY Flag and AEMPTY Flag Assertion

VJTAG**JTAG Supply Voltage**

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND. It should be noted that VCC is required to be powered for JTAG operation; VJTAG alone is insufficient. If a device is in a JTAG chain of interconnected boards, the board containing the device can be powered down, provided both VJTAG and VCC to the part remain powered; otherwise, JTAG signals will not be able to transition the device, even in bypass mode.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

VPUMP**Programming Supply Voltage**

For programming, VPUMP should be 3.3 V nominal. During normal device operation, VPUMP can be left floating or can be tied (pulled up) to any voltage between 0 V and the VPUMP maximum. Programming power supply voltage (VPUMP) range is listed in the datasheet.

When the VPUMP pin is tied to ground, it will shut off the charge pump circuitry, resulting in no sources of oscillation from the charge pump circuitry.

For proper programming, 0.01 μ F and 0.33 μ F capacitors (both rated at 16 V) are to be connected in parallel across VPUMP and GND, and positioned as close to the FPGA pins as possible.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

User-Defined Supply Pins

VREF**I/O Voltage Reference**

Reference voltage for I/O minibanks. VREF pins are configured by the user from regular I/Os, and any I/O in a bank, except JTAG I/Os, can be designated the voltage reference I/O. Only certain I/O standards require a voltage reference—HSTL (I) and (II), SSTL2 (I) and (II), SSTL3 (I) and (II), and GTL/GTL+. One VREF pin can support the number of I/Os available in its minibank.

User Pins

I/O**User Input/Output**

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Input and output signal levels are compatible with the I/O standard selected.

During programming, I/Os become tristated and weakly pulled up to VCCI. With VCCI, VMV, and VCC supplies continuously powered up, when the device transitions from programming to operating mode, the I/Os are instantly configured to the desired user configuration.

Unused I/Os are configured as follows:

- Output buffer is disabled (with tristate value of high impedance)
- Input buffer is disabled (with tristate value of high impedance)
- Weak pull-up is programmed

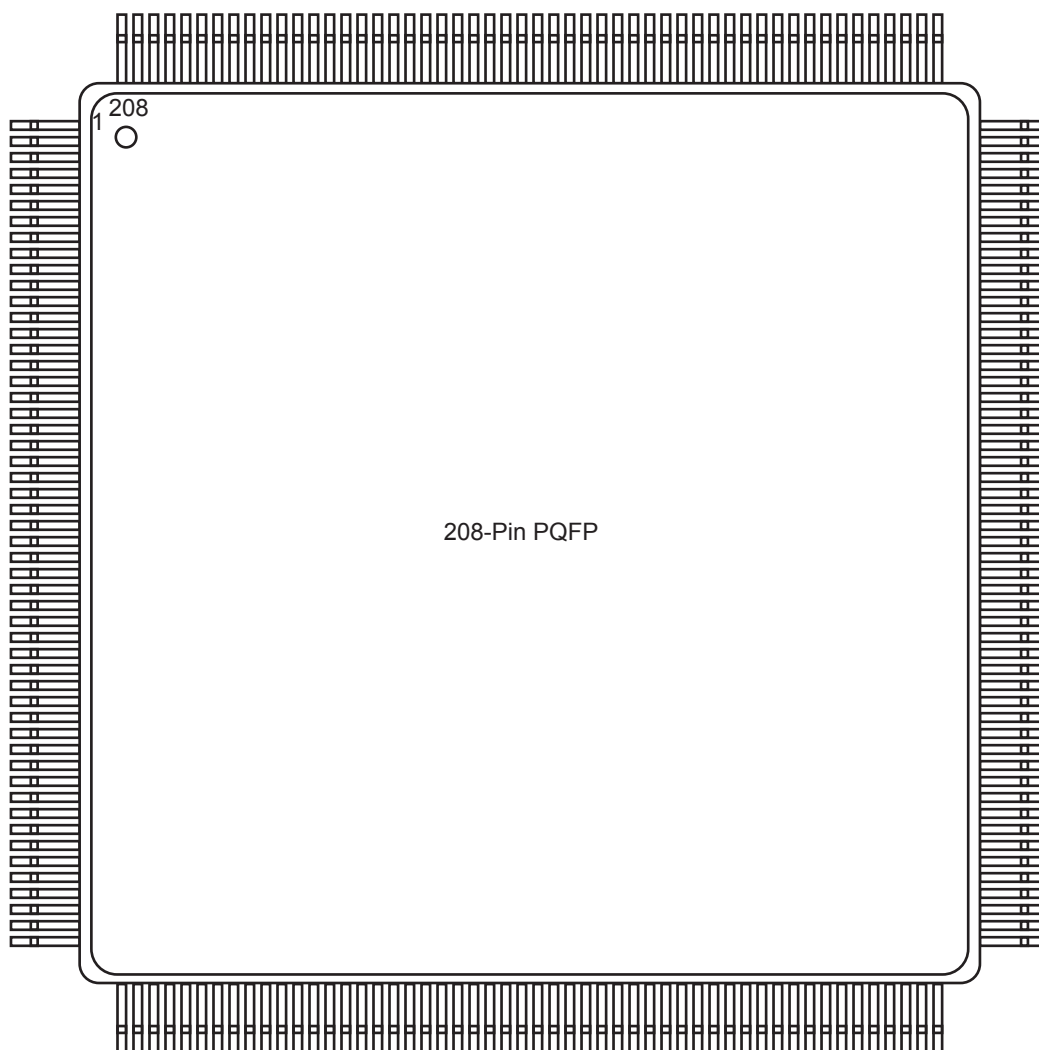
GL**Globals**

GL I/Os have access to certain clock conditioning circuitry (and the PLL) and/or have direct access to the global network (spines). Additionally, the global I/Os can be used as regular I/Os, since they have identical capabilities. Unused GL pins are configured as inputs with pull-up resistors.

See more detailed descriptions of global I/O connectivity in the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" chapter of the *ProASIC3E FPGA Fabric User's Guide*. All inputs labeled GC/GF are direct inputs into the quadrant clocks. For example, if GAA0 is used for an input, GAA1 and GAA2 are no longer available for input to the quadrant globals. All inputs labeled GC/GF are direct inputs into the chip-level globals, and the rest are connected to the quadrant globals. The inputs to the global network are multiplexed, and only one input can be used as a global input.

4 – Package Pin Assignments

PQ208



Note: This is the top view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/products/fpga-soc/solutions>.

PQ208	
Pin Number	A3PE600 Function
1	GND
2	GNDQ
3	VMV7
4	GAB2/IO133PSB7V1
5	GAA2/IO134PDB7V1
6	IO134NDB7V1
7	GAC2/IO132PDB7V1
8	IO132NDB7V1
9	IO130PDB7V1
10	IO130NDB7V1
11	IO127PDB7V1
12	IO127NDB7V1
13	IO126PDB7V0
14	IO126NDB7V0
15	IO124PSB7V0
16	VCC
17	GND
18	VCCIB7
19	IO122PPB7V0
20	IO121PSB7V0
21	IO122NPB7V0
22	GFC1/IO120PSB7V0
23	GFB1/IO119PDB7V0
24	GFB0/IO119NDB7V0
25	VCOMPLF
26	GFA0/IO118NPB6V1
27	VCCPLF
28	GFA1/IO118PPB6V1
29	GND
30	GFA2/IO117PDB6V1
31	IO117NDB6V1
32	GFB2/IO116PPB6V1
33	GFC2/IO115PPB6V1
34	IO116NPB6V1
35	IO115NPB6V1
36	VCC

PQ208	
Pin Number	A3PE600 Function
37	IO112PDB6V1
38	IO112NDB6V1
39	IO108PSB6V0
40	VCCIB6
41	GND
42	IO106PDB6V0
43	IO106NDB6V0
44	GEC1/IO104PDB6V0
45	GEC0/IO104NDB6V0
46	GEB1/IO103PPB6V0
47	GEA1/IO102PPB6V0
48	GEB0/IO103NPB6V0
49	GEA0/IO102NPB6V0
50	VMV6
51	GNDQ
52	GND
53	VMV5
54	GNDQ
55	IO101NDB5V2
56	GEA2/IO101PDB5V2
57	IO100NDB5V2
58	GEB2/IO100PDB5V2
59	IO99NDB5V2
60	GEC2/IO99PDB5V2
61	IO98PSB5V2
62	VCCIB5
63	IO96PSB5V2
64	IO94NDB5V1
65	GND
66	IO94PDB5V1
67	IO92NDB5V1
68	IO92PDB5V1
69	IO88NDB5V0
70	IO88PDB5V0
71	VCC

PQ208	
Pin Number	A3PE600 Function
72	VCCIB5
73	IO85NPB5V0
74	IO84NPB5V0
75	IO85PPB5V0
76	IO84PPB5V0
77	IO83NPB5V0
78	IO82NPB5V0
79	IO83PPB5V0
80	IO82PPB5V0
81	GND
82	IO80NDB4V1
83	IO80PDB4V1
84	IO79NPB4V1
85	IO78NPB4V1
86	IO79PPB4V1
87	IO78PPB4V1
88	VCC
89	VCCIB4
90	IO76NDB4V1
91	IO76PDB4V1
92	IO72NDB4V0
93	IO72PDB4V0
94	IO70NDB4V0
95	GDC2/IO70PDB4V0
96	IO68NDB4V0
97	GND
98	GDA2/IO68PDB4V0
99	GDB2/IO69PSB4V0
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV4
105	GND
106	VPUMP
107	GNDQ

PQ208	
Pin Number	A3PE3000 Function
118	IO134NDB3V2
119	IO134PDB3V2
120	IO132NDB3V2
121	IO132PDB3V2
122	GND
123	VCCIB3
124	GCC2/IO117PSB3V0
125	GCB2/IO116PSB3V0
126	NC
127	IO115NDB3V0
128	GCA2/IO115PDB3V0
129	GCA1/IO114PPB3V0
130	GND
131	VCCPLC
132	GCA0/IO114NPB3V0
133	VCOMPLC
134	GCB0/IO113NDB2V3
135	GCB1/IO113PDB2V3
136	GCC1/IO112PSB2V3
137	IO110NDB2V3
138	IO110PDB2V3
139	IO106PSB2V3
140	VCCIB2
141	GND
142	VCC
143	IO99NDB2V2
144	IO99PDB2V2
145	IO96NDB2V1
146	IO96PDB2V1
147	IO91NDB2V1
148	IO91PDB2V1
149	IO88NDB2V0
150	IO88PDB2V0
151	GBC2/IO84PSB2V0
152	GBA2/IO82PSB2V0
153	GBB2/IO83PSB2V0
154	VMV2
155	GNDQ
156	GND

PQ208	
Pin Number	A3PE3000 Function
157	VMV1
158	GNDQ
159	GBA1/IO81PDB1V4
160	GBA0/IO81NDB1V4
161	GBB1/IO80PDB1V4
162	GND
163	GBB0/IO80NDB1V4
164	GBC1/IO79PDB1V4
165	GBC0/IO79NDB1V4
166	IO74PDB1V4
167	IO74NDB1V4
168	IO70PDB1V3
169	IO70NDB1V3
170	VCCIB1
171	VCC
172	IO56PSB1V1
173	IO55PDB1V1
174	IO55NDB1V1
175	IO54PDB1V1
176	IO54NDB1V1
177	IO40PDB0V4
178	GND
179	IO40NDB0V4
180	IO37PDB0V4
181	IO37NDB0V4
182	IO35PDB0V4
183	IO35NDB0V4
184	IO32PDB0V3
185	IO32NDB0V3
186	VCCIB0
187	VCC
188	IO28PDB0V3
189	IO28NDB0V3
190	IO24PDB0V2
191	IO24NDB0V2
192	IO21PSB0V2
193	IO16PDB0V1
194	IO16NDB0V1
195	GND

PQ208	
Pin Number	A3PE3000 Function
196	IO11PDB0V1
197	IO11NDB0V1
198	IO08PDB0V0
199	IO08NDB0V0
200	VCCIB0
201	GAC1/IO02PDB0V0
202	GAC0/IO02NDB0V0
203	GAB1/IO01PDB0V0
204	GAB0/IO01NDB0V0
205	GAA1/IO00PDB0V0
206	GAA0/IO00NDB0V0
207	GNDQ
208	VMV0

FG324	
Pin Number	A3PE3000 FBGA
G1	GND
G2	IO287PDB7V1
G3	IO287NDB7V1
G4	IO283PPB7V1
G5	VCCIB7
G6	IO279PDB7V0
G7	IO291NPB7V2
G8	VCC
G9	IO26NDB0V3
G10	IO34NDB0V4
G11	VCC
G12	IO94NPB2V1
G13	IO98PDB2V2
G14	VCCIB2
G15	GCC0/IO112NPB2V3
G16	IO104PDB2V2
G17	IO104NDB2V2
G18	GND
H1	IO267PDB6V4
H2	VCCIB7
H3	IO283NPB7V1
H4	GFB1/IO274PPB7V0
H5	GND
H6	IO279NDB7V0
H7	VCC
H8	VCC
H9	GND
H10	GND
H11	VCC
H12	VCC
H13	IO98NDB2V2
H14	GND
H15	GCB1/IO113PDB2V3
H16	GCC1/IO112PPB2V3
H17	VCCIB2
H18	IO108PDB2V3

FG324	
Pin Number	A3PE3000 FBGA
J1	IO267NDB6V4
J2	GFA0/IO273NDB6V4
J3	VCOMPLF
J4	GFA2/IO272PDB6V4
J5	GFB0/IO274NPB7V0
J6	GFC0/IO275NDB7V0
J7	GFC1/IO275PDB7V0
J8	GND
J9	GND
J10	GND
J11	GND
J12	GCA2/IO115PDB3V0
J13	GCA1/IO114PDB3V0
J14	GCA0/IO114NDB3V0
J15	GCB0/IO113NDB2V3
J16	VCOMPLC
J17	IO120NPB3V0
J18	IO108NDB2V3
K1	IO263PDB6V3
K2	GFA1/IO273PDB6V4
K3	VCCPLF
K4	IO272NDB6V4
K5	GFC2/IO270PPB6V4
K6	GFB2/IO271PDB6V4
K7	IO271NDB6V4
K8	GND
K9	GND
K10	GND
K11	GND
K12	IO115NDB3V0
K13	GCB2/IO116PDB3V0
K14	IO116NDB3V0
K15	GCC2/IO117PDB3V0
K16	VCCPLC
K17	IO124NPB3V1
K18	IO120PPB3V0

FG324	
Pin Number	A3PE3000 FBGA
L1	IO263NDB6V3
L2	VCCIB6
L3	IO259PDB6V3
L4	IO259NDB6V3
L5	GND
L6	IO270NPB6V4
L7	VCC
L8	VCC
L9	GND
L10	GND
L11	VCC
L12	VCC
L13	IO132PDB3V2
L14	GND
L15	IO117NDB3V0
L16	IO128NPB3V1
L17	VCCIB3
L18	IO124PPB3V1
M1	GND
M2	IO255PDB6V2
M3	IO255NDB6V2
M4	IO251PPB6V2
M5	VCCIB6
M6	GEB0/IO235NDB6V0
M7	GEB1/IO235PDB6V0
M8	VCC
M9	IO192PPB4V4
M10	IO154NPB4V0
M11	VCC
M12	GDA0/IO153NPB3V4
M13	IO132NDB3V2
M14	VCCIB3
M15	IO134NDB3V2
M16	IO134PDB3V2
M17	IO128PPB3V1
M18	GND

FG484		FG484		FG484	
Pin Number	A3PE3000 Function	Pin Number	A3PE3000 Function	Pin Number	A3PE3000 Function
A1	GND	AA15	IO170PDB4V2	B7	IO14PDB0V1
A2	GND	AA16	IO166NDB4V1	B8	IO18NDB0V2
A3	VCCIB0	AA17	IO166PDB4V1	B9	IO24NDB0V2
A4	IO10NDB0V1	AA18	IO160NDB4V0	B10	IO34PDB0V4
A5	IO10PDB0V1	AA19	IO160PDB4V0	B11	IO40PDB0V4
A6	IO16NDB0V1	AA20	IO158NPB4V0	B12	IO46NDB1V0
A7	IO16PDB0V1	AA21	VCCIB3	B13	IO54NDB1V1
A8	IO18PDB0V2	AA22	GND	B14	IO62NDB1V2
A9	IO24PDB0V2	AB1	GND	B15	IO62PDB1V2
A10	IO28NDB0V3	AB2	GND	B16	IO68NDB1V3
A11	IO28PDB0V3	AB3	VCCIB5	B17	IO68PDB1V3
A12	IO46PDB1V0	AB4	IO216NDB5V2	B18	IO72PDB1V3
A13	IO54PDB1V1	AB5	IO216PDB5V2	B19	IO74PDB1V4
A14	IO56NDB1V1	AB6	IO210NDB5V2	B20	IO76NPB1V4
A15	IO56PDB1V1	AB7	IO210PDB5V2	B21	VCCIB2
A16	IO64NDB1V2	AB8	IO208NDB5V1	B22	GND
A17	IO64PDB1V2	AB9	IO208PDB5V1	C1	VCCIB7
A18	IO72NDB1V3	AB10	IO197NDB5V0	C2	IO303PDB7V3
A19	IO74NDB1V4	AB11	IO197PDB5V0	C3	IO305PDB7V3
A20	VCCIB1	AB12	IO174NDB4V2	C4	IO06NPB0V0
A21	GND	AB13	IO174PDB4V2	C5	GND
A22	GND	AB14	IO172NDB4V2	C6	IO12NDB0V1
AA1	GND	AB15	IO172PDB4V2	C7	IO12PDB0V1
AA2	VCCIB6	AB16	IO168NDB4V1	C8	VCC
AA3	IO228PDB5V4	AB17	IO168PDB4V1	C9	VCC
AA4	IO224PDB5V3	AB18	IO162NDB4V1	C10	IO34NDB0V4
AA5	IO218NDB5V3	AB19	IO162PDB4V1	C11	IO40NDB0V4
AA6	IO218PDB5V3	AB20	VCCIB4	C12	IO48NDB1V0
AA7	IO212NDB5V2	AB21	GND	C13	IO48PDB1V0
AA8	IO212PDB5V2	AB22	GND	C14	VCC
AA9	IO198PDB5V0	B1	GND	C15	VCC
AA10	IO198NDB5V0	B2	VCCIB7	C16	IO70NDB1V3
AA11	IO188PPB4V4	B3	IO06PPB0V0	C17	IO70PDB1V3
AA12	IO180NDB4V3	B4	IO08NDB0V0	C18	GND
AA13	IO180PDB4V3	B5	IO08PDB0V0	C19	IO76PPB1V4
AA14	IO170NDB4V2	B6	IO14NDB0V1	C20	IO88NDB2V0

Revision	Changes	Page
Advance v0.5 (continued)	The "RESET" section was updated.	2-25
	The "RESET" section was updated.	2-27
	The "Introduction" of the "Introduction" section was updated.	2-28
	PCI-X 3.3 V was added to the Compatible Standards for 3.3 V in Table 2-11 • VCCI Voltages and Compatible Standards	2-29
	Table 2-35 • ProASIC3E I/O Features was updated.	2-54
	The "Double Data Rate (DDR) Support" section was updated to include information concerning implementation of the feature.	2-32
	The "Electrostatic Discharge (ESD) Protection" section was updated to include testing information.	2-35
	Level 3 and 4 descriptions were updated in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices.	2-64
	The notes in Table 2-45 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3E Devices were updated.	2-64
	The "Simultaneous Switching Outputs (SSOs) and Printed Circuit Board Layout" section is new.	2-41
	A footnote was added to Table 2-37 • Maximum I/O Frequency for Single-Ended and Differential I/Os in All Banks in ProASIC3E Devices (maximum drive strength and high slew selected).	2-55
	Table 2-48 • ProASIC3E I/O Attributes vs. I/O Standard Applications	2-81
	Table 2-55 • ProASIC3 I/O Standards—SLEW and Output Drive (OUT_DRIVE) Settings	2-85
	The "x" was updated in the "Pin Descriptions" section.	2-50
	The "VCC Core Supply Voltage" pin description was updated.	2-50
	The "VMVx I/O Supply Voltage (quiet)" pin description was updated to include information concerning leaving the pin unconnected.	2-50
	EXTFB was removed from Figure 2-24 • ProASIC3E CCC Options.	2-24
	The CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT} was updated in Table 2-13 • ProASIC3E CCC/PLL Specification.	2-30
	EXTFB was removed from Figure 2-27 • CCC/PLL Macro.	2-28
	The LVPECL specification in Table 2-45 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3E Devices was updated.	2-64
	Table 2-15 • Levels of Hot-Swap Support was updated.	2-34
	The "Cold-Sparing Support" section was updated.	2-34
	"Electrostatic Discharge (ESD) Protection" section was updated.	2-35
	The VJTAG and I/O pin descriptions were updated in the "Pin Descriptions" section.	2-50
	The "VJTAG JTAG Supply Voltage" pin description was updated.	2-50
	The "VPUMP Programming Supply Voltage" pin description was updated to include information on what happens when the pin is tied to ground.	2-50

Revision	Changes	Page
Advance v0.3 (continued)	The "Methodology" section was updated.	3-9
	The A3PE3000 "208-Pin PQFP" pin table was updated.	4-6